## Rapid-temperature-rising induced reduction of NiO film grown on Ni(111) surface IMRAM Tohoku Univ.<sup>1</sup>, JAEA<sup>2</sup>, o(M1)Bingruo Zhang<sup>1</sup>, Nobuhisa Kamata<sup>1</sup>, Shuichi Ogawa<sup>1</sup>,

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To clarify the potential of Ni surfaces as an alternative catalyst of Pt for exhaust gases of automobiles, the oxidation and reduction reaction kinetics on Ni(111) surfaces were investigated by X-ray photoelectron spectroscopy using synchrotron radiation (hv = 1100 eV) at BL23SU, SPring-8. By annealing at 700°C under H<sub>2</sub> atmosphere at  $P_{\text{H2}} = 9 \times 10^{-4}$  Pa for 600 s, there were no traces of carbon, oxygen, sulfur, and chlorine contaminants within the detection limit.

For the clean Ni(111) surface, the Ni  $2p_{3/2}$ photoelectron spectrum is fitted well with an asymmetric Voigt function (Peak A) with 6-eV satellite as demonstrated in Fig. 1(a). [1]. After oxidizing the Ni(111) surface, four symmetric Voigt functions with different widths are necessary for obtaining a good accordance with the measured spectrum in addition to Peak A as separated in Fig 1(b). Peak B, C, and D is ascribed to charge transfer satellites from O 2p to Ni 3d <u>c3d<sup>9</sup>L</u>, nonlocal <u>c3d<sup>9</sup>L</u>, and <u>c3d<sup>10</sup>L<sup>2</sup></u>, states, respectively, where c and L denote a hole in Ni 2p and O 2p, respectively. Peak E is a component with no charge transfer, <u>c</u>3d<sup>8</sup>. The thickness of the NiO film,  $d_{\rm NiO}$ , were obtained from the photoelectron intensity ratio of the sum of the  $\underline{c}3d^{9}\underline{L}$ , nonlocal  $\underline{c}3d^{9}\underline{L}$ ,  $\underline{c}3d^{10}\underline{L}^{2}$ , and c3d<sup>8</sup> components to Ni metal component as shown in Fig, 2. The  $d_{\text{NiO}}$  shows a parabolic dependence on time, indicating that the NiO growth is governed by O diffusion through the NiO layer. When raising the temperature from 350 to 700°C at the same time of stopping O<sub>2</sub> supply, a steep decrease of  $d_{\text{NiO}}$  is caused only during the rapid temperature rising and then  $d_{\rm NiO}$ 







(b)  $d_{\text{NiO}}$ .

shows no significant decrease during the isothermal annealing at 700 °C. The observed rapidtemperature-rising induced reduction of the NiO film is considered in terms of the difference of thermal expansion coefficient between Ni and NiO, surface NiO component and O<sub>2</sub> desorption from the NiO surface, which were examined by changing the surface sensitive ( $\theta = 0^\circ$  and 70°). [1] I. Preda et al., Phys. Rev. B 77, 075411 (2008).